TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE

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FOR MUTING AND SWITCHING APPLICATIONS

• High Emitter-Base Voltage : VEBO = 25V (Min.)

• High Reverse h_{FE} : $h_{FE}=150$ (Typ.) ($V_{CE}=-2V$, $I_{C}=-4mA$)

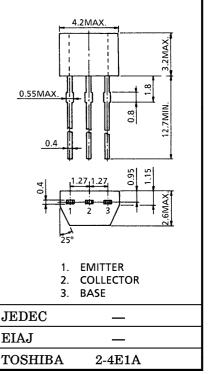
• Low On Resistance : $R_{ON}=1\Omega$ (Typ.) ($I_B=5mA$)

• Small Package

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	50	V
Collector-Emitter Voltage	v_{CEO}	20	V
Emitter-Base Voltage	$V_{ m EBO}$	25	V
Collector Current	$I_{\mathbf{C}}$	300	mA
Base Current	$I_{\mathbf{B}}$	60	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	200	mW
Junction Temperature	Tj	125	$^{\circ}\mathrm{C}$
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Unit in mm



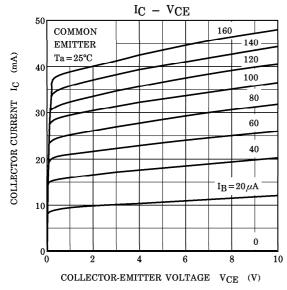
Weight: 0.13g

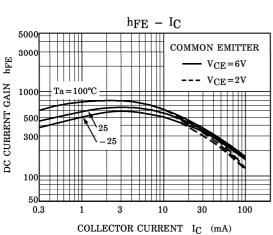
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

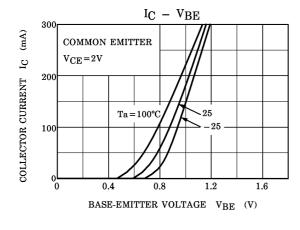
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current		I_{CBO}	$V_{CB} = 50V, I_E = 0$			0.1	μ A	
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 25V, I_C = 0$	_	_	0.1	μ A	
DC Current Gain		h _{FE} (Note)	$V_{CE}=2V$, $I_{C}=4mA$	200	_	1200		
Collector-Emitter Sturation Voltage		V _{CE} (sat)	$I_C=30$ mA, $I_B=3$ mA	_	0.042	0.1	V	
Base-Emitter Voltage		$v_{ m BE}$	$V_{CE}=2V$, $I_{C}=4mA$	_	0.61	_	V	
Transition Frequency		$\mathbf{f_T}$	$V_{CE}=6V$, $I_{C}=4mA$	_	30	_	MHz	
Collector Output Capacitance		C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$	_	4.8	7	pF	
Switching Time	Turn-on Time	ton	INPUT $4k\Omega$ OUTPUT $10V$ $1\mu s$ V_{BB} V_{CC} $=-3V$ $=12V$ DUTY CYCLE $<2\%$	_	160			
	Storage Time	$ m t_{stg}$		_	500	_	ns	
	Fall Time	t_f		_	130	_		

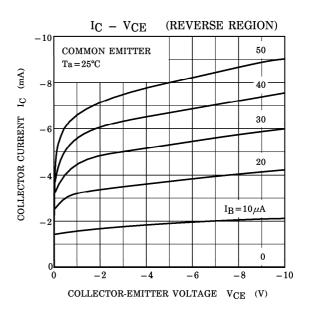
Note : hFE Classification A : 200~700, B : 350~1200

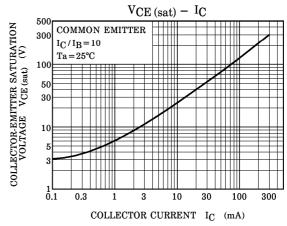
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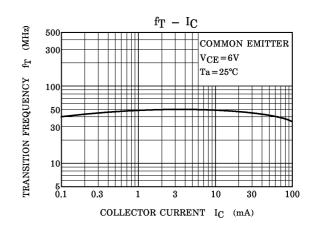




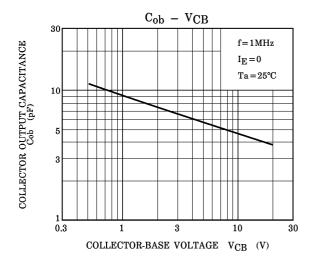


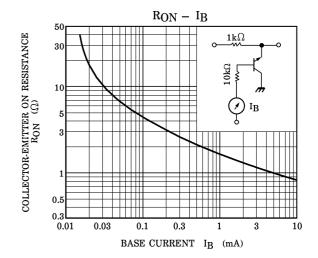


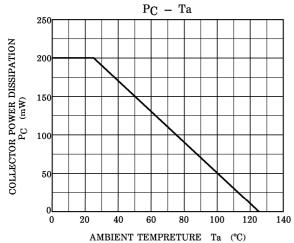




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